

50V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage

50 V

Current

360mA

Features

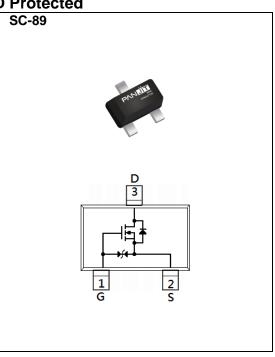
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@500mA<1.45\Omega$
- R_{DS(ON)} , V_{GS}@4.5V, I_D@200mA<1.95Ω
- R_{DS(ON)} , V_{GS}@2.5V, I_D@100mA<4Ω
- $R_{DS(ON)}$, $V_{GS}@1.8V$, $I_D@10mA<6\Omega$
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: SC-89 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0026 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS		
Drain-Source Voltage	V _{DS}	50	V		
Gate-Source Voltage	V _G s	<u>+</u> 20			
Continuous Drain Current		ID	360	mA	
Pulsed Drain Current		I _{DM}	1200		
Power Dissipation	T _A =25°C	_	300	mW	
	Derate above 25°C	P _D	2.4	mW/°C	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~150	°C	
Typical Thermal Resistance - Junction to Ambient ^(Note 3)		Reja	417	°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	50	-	- V		
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} , I _D =250uA	0.5	0.86	1	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =500mA	-	1.2	1.45	Ω	
		V _{GS} =4.5V, I _D =200mA	-	1.3	1.95		
		V _{GS} =2.5V, I _D =100mA	-	1.7	4		
		V _{GS} =1.8V, I _D =10mA	-	4	6		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =50V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 10		
Dynamic ^(Note 4)							
Total Gate Charge	Q_g	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	0.95	-	nC	
Gate-Source Charge	Q_{gs}	V _{DS} =25V, I _D =500mA, V _{GS} =4.5V ^(Note 1,2)	-	0.34	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5 V(Note 1,2)	-	0.32	-		
Input Capacitance	Ciss)/ OF)/)/ O)/	-	36	-	pF	
Output Capacitance	Coss	V _{DS} =25V, V _{GS} =0V,	-	11	-		
Reverse Transfer Capacitance	Crss	f=1MHz	-	6.6	-		
Turn-On Delay Time	td _(on))/ O5)/ L 500 ·· A	-	2.3	-		
Turn-On Rise Time	tr	V _{DD} =25V, I _D =500mA,	-	20	-	ns	
Turn-Off Delay Time	td _(off)	$V_{GS}=10V$, $R_{G}=6\Omega^{(Note\ 1,2)}$	-	7	-		
Turn-Off Fall Time	tf	KG=012(Note 1,2)	-	20	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	500	mA	
Diode Forward Voltage	V _{SD}	Is=500mA, V _{GS} =0V	-	0.9	1.5	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper.
- 4. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

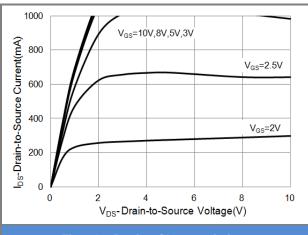


Fig.1 On-Region Characteristics

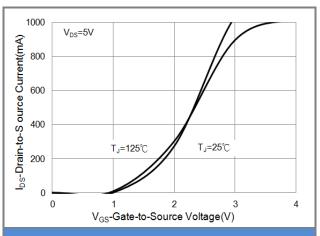


Fig.2 Transfer Characteristics

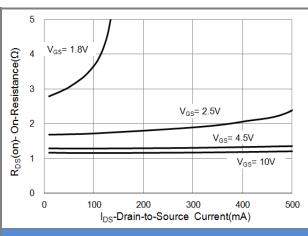


Fig.3 On-Resistance vs. Drain Current

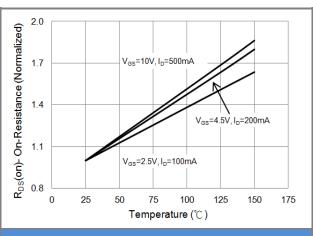
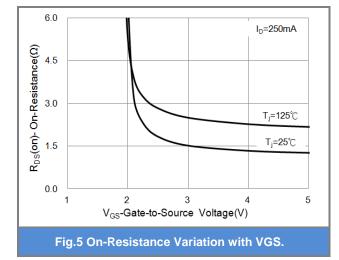
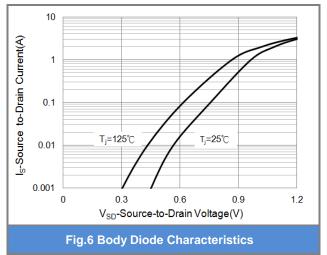


Fig.4 On-Resistance vs. Junction temperature





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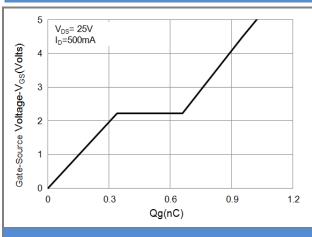


Fig.7 Gate-Charge Characteristics

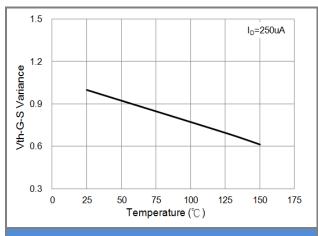


Fig.9 Threshold Voltage Variation with Temperature

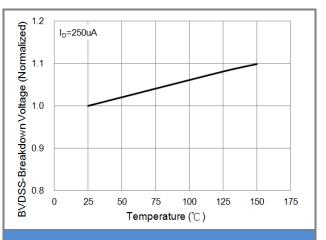


Fig.8 Breakdown Voltage Variation vs. Temperature

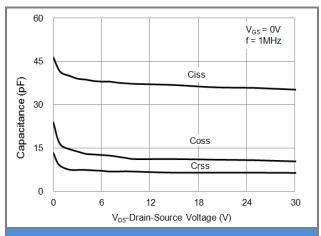


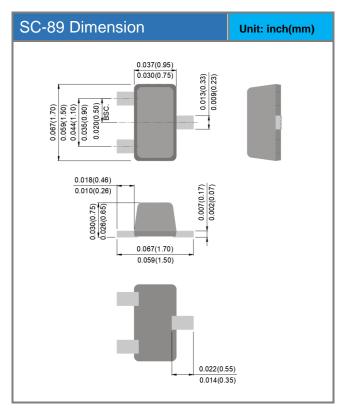
Fig.10 Capacitance vs. Drain-Source Voltage

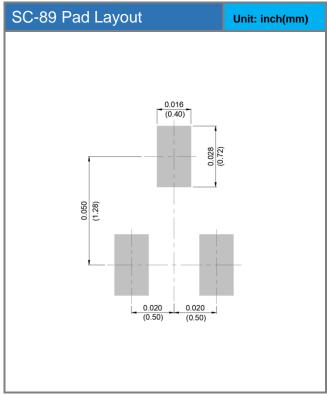


Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJE8438TB89	SC-89	4K pcs / 7" reel	E38

Packaging Information & Mounting Pad Layout







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